ADAG GAMENTE

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	USN	MC, lbra		LN14/24
3	Vate	····F	First/Second Semester B.E. Degree Examination, June/July 20)23
3/12	SAM.	ward ha	Basic Electronics	
	T:	ALU		1 400
	1111		hrs. Max. M ote: Answer any FIVE full questions, choosing ONE full question from each mo	arks: 100
o.		144		aute.
actic			Module-1	
ou, will be treated as maiplacife	1	a.	Explain how Zener diode can be used as a voltage Regulator with and wiresistance.	
1 45 11		b.	Define the following parameters and mention its ideal values for both half wave	(07 Marks) and bridge
כמוכר			rectifier	8
חבח			i) Ripple factorii) Power conversion Efficiency	
WIII			iii) PIV	(07 Marks)
ا ر		C.	Explain the working of Light Emitting Diode and mention its Applications.	(06 Marks)
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zg 1			OR	
111011	2		Draw the circuit diagram of a Full wave bridge rectifier and explain it.	(07 Marks)
IN SI		b.	Draw the functional block diagram of the 78XX series voltage regulator and n function of each block.	(07 Marks)
IALIOI		c.	Write the ideal diode, piecewise Linear model and approximate model of a I	
1 cdr			VI – characteristics.	(06 Marks)
חות /כ			Module-2	
1101 a	3	a.	Draw the Drain and Transfer Characteristics of N-channel JFET and explain it.	(07 Marks)
value		b. c.	Explain the working of CMOS inverter and also mention its Advantages.	(07 Marks)
1 10 0		C.	For JFET, $I_{DSS} = 6\text{mA}$, $V_p = -4.5\text{V}$, determine drain current at $V_{GS} = -2\text{V}$ and -4V	(06 Marks)
ррса				
Any teveaning or identification, appea			OR	
псап	4	a.	Draw the characteristics of SCR and explain it.	(07 Marks)
nemn		b.	Explain the construction and operation of N-channel Enhancement type MOSFET	
0 10		C.	Compare FET with BJT and also write the square Law expression for drain curren	it. (06 Marks)
Zalili)		3		,
ICVO			Module-3	
CITY I	5	a.	Define the following op-amp parameters and mention its ideal values	
7		1	i) CMRR ii) Slew rate iii) SVRR/PSRR iv) Input bias current.	(08 Marks)
		b.	Design an adder circuit using op-amp to get the output $V_0 = -(0.1V_1 + V_2 + 10V_3)$ $R_f = 10K\Omega$ and V_1 , V_2 , V_3 are the input voltages.	
		C.	What is differentiator and obtain the expression of output voltage using op-amp.	(06 Marks) (06 Marks)

OR

6 a. What are the op-amp input modes and explain it.

(08 Marks)

b. For the op-amp circuit shown in Fig Q6(b), find V_0' and V_0

100KV



Fig Q6(b)

(06 Marks)

c. Derive the expression of closed loop voltage gain of a non-inverting amplifier using op-amp.

(06 Marks)

Module-4

7 a. Explain the operation of BJT can be used as a switch.

(07 Marks)

- a. Explain the operation of Bar can be ased as a street of Mention the properties and advantages of Negative feedback.
 b. Mention the properties and advantages of Negative feedback.
- c. State Barkhausen condition for oscillator. Write the circuit diagram, equations for sustained oscillation and frequency of oscillation. (06 Marks)

OR

- 8 a. Explain the operation of a Astable Multivibrator using IC-555 Timer and also write the equation of frequency of oscillation. (07 Marks)
 - b. Draw the transistor switch circuit to switch ON/OFF on LED and explain it. (07 Marks)
 - c. Design a wein bridge oscillator to get oscillation frequency of 5KHz. Assume $R=100 K\Omega$ and $R_1=200 K\Omega$.

Module-5

- 9 a. Mention the differences between Analog and digital signals. Write the waveform for converting analog into digital signal. (07 Marks)
 - b. Convert the following:
 - i) (FA876)₁₆ in to Binary form
 - ii) (345.75)₁₀ into Hexadecimal
 - iii) $(0.705)_{10}$ into octal

(06 Marks)

c. What is multiplexer? Implement 8 to 1 multiplexer using basic Gates.

(07 Marks)

OR

- 10 a. Implement the following Boolean functions
 - i) $F = (A + C\overline{D} + \overline{D}\overline{E})$ using NAND Gates ii) $F = (\overline{C} + A)(\overline{C} + B)$ using NOR – Gates

(07 Marks)

b. Explain the operation of a JK-master slave flip-flop.

(07 Marks)

c. Draw the block diagram of a cellular mobile radio unit and mention the functions of each block.

(06 Marks)

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